

What Is Claimed Is:

1. A rectifier system, in particular a rectifier bridge for a three-phase generator, comprising a plurality of rectifier elements,

wherein specifiable rectifier elements are different from the other rectifier elements in at least one property.

2. The rectifier system as recited in Claim 1, wherein the properties of the rectifier elements are selected in such a way that the ripple of the voltage which can be picked off at the output of the rectifier system, or the ripple of the current which can be picked off, is minimal or is at least reduced.

3. The rectifier system as recited in Claim 1 or 2, wherein the property with regard to which the rectifier elements at least differ from one another is the switching time or the reverse recovery switching time ( $t_{rr}$ ) and/or the current density and/or the chip area and/or the chip thickness and/or the breakdown voltage ( $Z_U$ ) and/or the internal resistance ( $R_I$ ) and/or the path resistance and/or another property which is suited for reducing ripple.

4. The rectifier system as recited in one of the preceding claims, wherein the rectifier elements are diodes, Zener diodes in particular.

5. The rectifier system as recited in one of the preceding claims, wherein specifiable rectifier elements are parallel connections of two diodes having different properties.

6. The rectifier system as recited in Claim 5, wherein the two diodes have different switching times or different reverse recovery switching times ( $t_{rr}$ ).
7. The rectifier system as recited in one of the preceding claims, wherein the different reverse recovery characteristics are achieved by using diodes having different breakdown voltages.
8. The rectifier system as recited in Claim 7, wherein one of the two diodes is in the Zener voltage range of 18 volts through 50 volts and the other is in the Zener voltage range of 100 volts through 800 volts.
9. The rectifier system as recited in one of the preceding claims, wherein different current densities of the rectifier elements are implemented through different chip areas and/or chip thicknesses and/or path resistances.
10. The rectifier system as recited in one of the preceding claims, wherein twelve diodes are used as rectifier elements in a rectifier bridge; in each instance, two diodes having different properties being connected in parallel.
11. The rectifier system as recited in one of the preceding claims, wherein in a rectifier bridge having twelve diodes, either only the positive or only the negative diodes have parallel connections of two diodes possessing different properties.
12. The rectifier system as recited in one of the preceding claims,

wherein four diodes having the first property and eight diodes having the second property are used in a rectifier bridge having twelve diodes.

13. The rectifier system as recited in Claim 11, wherein the rectifier bridge has nine diodes.